

Synthesis of high density sub-10 μm ($\text{Ba}_{0.85}\text{Ca}_{0.15}$) ($\text{Zr}_{0.1}\text{T}_{i0.9}$) O_3 - $x\text{CeO}_2$ lead-free ceramics using a two-step sintering technique

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Synthesis of high density sub-10 μm $(\text{Ba}_{0.85}\text{Ca}_{0.15})(\text{Zr}_{0.1}\text{T}_{i0.9})\text{O}_3\text{-xCeO}_2$ lead-free ceramics using a two-step sintering technique

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ABSTRACT

$(\text{Ba}_{0.85}\text{Ca}_{0.15})(\text{Zr}_{0.1}\text{T}_{i0.9})\text{O}_3\text{-xCeO}_2$ (BCZTCe) lead-free piezoelectric ceramics were processed conventionally using a two-step sintering technique. The results suggest that two-step sintering is an effective technique to acquire a high density (99%) homogeneous microstructure with sub-10 μm grain size. The low CeO_2 content (0.07 wt.%) facilitates good functional properties at low sintering conditions of $T_1 = 1400^\circ\text{C}/30\text{ min}$ & $T_2 = 1275^\circ\text{C}/4\text{ h}$, in which $d_{33} = 353 \pm 7\text{ pC/N}$, $k_p = 40\%$, $\epsilon_r = 3393 \pm 100$, $\tan \delta = 0.039$, $T_C = 96.5^\circ\text{C}$, $P_r = 11.45\ \mu\text{C}/\text{cm}^2$, $E_C = 2.32\ \text{kV}/\text{cm}$ and a large strain of 0.18%. These results indicate that BCZTCe ceramics are a promising lead-free piezoelectric substitute for room temperature device applications.

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1. Introduction

Piezoelectric materials are smart functional materials that can convert energy (mechanical to electrical or vice versa) and are used in a variety of electronic devices [1–4]. Among these lead zirconate titanate (PZT) and related materials are dominant in terms of use of their piezoelectric properties in sensors, actuators, fuel injectors, transducers, etc [1,3]. Due to the lead (Pb) toxicity and its non-environmentally friendly nature, a search has begun to replace PZT and related systems [3,4]. Lead-derived materials exhibit a morphotropic phase boundary (MPB), which generates enhanced ferroelectric and piezoelectric properties. Hence, work on lead-free systems has also concentrated on developing systems with an MPB.

$(\text{Ba}_{0.85}\text{Ca}_{0.15})(\text{Zr}_{0.1}\text{T}_{i0.9})\text{O}_3$ (BCZT) lead-free material system developed by Liu and Ren in 2009 showed excellent piezoelectric properties: $d_{33} \sim 620\text{ pC/N}$ [5]. Several groups have tried to reproduce these results since then but could not achieve the same results with pure BCZT and other solid solutions ($d_{33} < 470\text{ pC/N}$) [6–11]. A possible reason behind their inferior results may be the stoichiometric ratio, method of synthesis and sintering techniques used for the preparation of raw powders and the final sintered body. The method used in previous publications does not guarantee stoichiometric homogeneity during processing, which can cause fluctuation of the piezoelectric properties. These techniques include the solid-state reaction method [12], hot pressing method [13], modified pechini method [14] and the application of various processing parameters such as calcination temperatures [15].

Piezoelectric constants fluctuate as 500–650 (pC/N) from these methods which is mainly due to fluctuations in the initial particle size, density and pore size distribution.

Previous reports indicate that the grain size can greatly affect dielectric and piezoelectric responses in piezoceramics [16–19]. To reduce the sintering temperature of BCZT ceramics, different dopants were used as sintering aids, while maintaining good piezoelectric properties [20–23]. Grain-size deviations can also cause variability in the functional properties [24,25].

There are always experimental complications in synthesizing a series of dense BaTiO_3 (BT) based lead-free ceramics with different desired values such as an average grain size using a sole source of BT powder as well as a single sintering technique [26]. Accordingly, different kinds of BT powder and sintering techniques have usually been combined, such as those described by Arlt et al. [27]. This may distress the consistency of the experimental results owing to the different characters of the obtained BT ceramics. To this approach, it is highly desirable in studying grain-size effects (sub-10 μm) to use a group of BT ceramics (Such as BCZT) that offers a very high final ceramic density and a uniform grain-size distribution in their microstructures in order to obtain good functional properties, in particular.

The present study is a follow-up to our previous study in which we prepared $(\text{Ba}_{0.85}\text{Ca}_{0.15})(\text{Zr}_{0.1}\text{T}_{i0.9})\text{O}_3\text{-xCeO}_2$ ceramics by the conventional method and conventional single-step sintering [28]. In that study, we found that a grain size of $\sim 13\ \mu\text{m}$ and density of $\sim 95\%$ were suitable for obtaining high piezoelectric

properties ($d_{33} > 500$ pC/N) at a lower sintering temperature of 1350°C/4 h while doping with CeO₂ [26]. Nonetheless, reports showing the effects of sub-10 µm grain sizes on the functional properties of (Ba_{0.85}Ca_{0.15}) (Zr_{0.1}Ti_{0.9}) O₃ ceramics are rare. However, reducing the grain size (<10 µm) while maintaining fairly good properties for BCZT ceramics is a challenge [29,30]. Thus, a two-step sintering technique was introduced in order to further reduce the grain size of these ceramics and study the effects on their functional properties. The main aim of the current study is to maintain grain size (<10 µm) with a homogeneous microstructure and obtain very high-density ceramics together with good piezoelectric, dielectric and ferroelectric properties. (Ba_{0.85}Ca_{0.15}) (Zr_{0.1}Ti_{0.9}) O₃ - xCeO₂ (x = 0, 0.02, 0.04, 0.07 wt.%) were prepared using a two-step sintering (TSS) technique. The microstructural, piezoelectric, dielectric and ferroelectric properties were systematically studied.

2. Experimental

(Ba_{0.85}Ca_{0.15}) (Zr_{0.1}Ti_{0.9}) O₃ - xCeO₂ (x = 0, 0.02, 0.04, 0.07 wt.%) materials were processed by the conventional solid-state reaction route. Raw materials of BaCO₃ (Dakram, Great Britain, 99.9%) CaCO₃ (Lachner, Czech Republic, 99.9%), ZrO₂ (Dakram, Great Britain, 99.9%), TiO₂ (Dakram, Great Britain, 99.9%) and CeO₂ (Sigma Aldrich, Great Britain, 99.9%) were dried in an oven (Lenton MMD/0229, England) at 220°C/1 h before weighing. The raw powders were then mixed with a horizontal ball mill using zirconia milling media and deionized water for 24 h. The resulting slurry was dried in the oven at 90°C for 15 h and then calcined in a muffle furnace (Lenton, 5696, England) at 1250°C for 2 h. Different concentrations of CeO₂ (0–0.07 wt.%), were added in four batches (30 gm each) of the calcined BCZT powders and re-milled in deionized water for 24 h. Approximately 5 wt.% of each binder, Duramax B1000 (Product No. 74821, Chesham Chemicals Ltd., UK), B1007 (Product No. 74823, Chesham Chemicals Ltd., UK) were added during the last hour of milling. The particle sizes were measured using a particle size analyzer (Gracell, Sympa Tec, Germany) and the average particle sizes of all batches were ~2 µm. Dried powder was then sieved (300 mesh, VWR, England) and uniaxially pressed at 155 MPa (Instron, 5507, England) into the green bodies using a 13 mm diameter cylindrical steel die (P.T. No. 3000, Specac, UK). The green bodies were finally sintered at different temperatures using a two-step sintering technique (TSS). In the first step the furnace is programmed for a rapid ramp-up rate 10°C/min to a set temperature T₁ (1350, 1400, 1450°C) with 30 min dwell in order to ensure the uniformity of the heat atmosphere inside the furnace chamber. The furnace was then cooled rapidly at 30°C/min to a lower temperature T₂. This temperature was set at 1275°C to prevent further grain growth and maintained

for 4 h. Finally, the temperature was ramped down to room temperature at a rate of 10°C/min. The relative densities were measured by the Archimedes method using the theoretical density (5.80 g/cm³) from XRD results. The phase structure of the sintered discs was examined by X-ray diffraction (Equinox 3000, INEL, France) with Cu-Kα radiation (λ = 1.54178 Å). A chromium (Cr) – gold (Au) coating was sputtered as electrodes using a sputter coater (K575X, Emitech, UK), and the samples were poled in silicon oil at 3 kV/mm for 10 min. The dielectric properties were measured with an impedance analyzer (4294, Agilent, USA) at 1 kHz. The piezoelectric constant was measured with a Berlincourt d₃₃ meter (YE2730A, Sinocera, China). The surface morphologies were observed by scanning electron microscopy (JEOL 6060LV, England). Ferroelectric P-E and S-E hysteresis were measured with an aixACCT Systems (GmbH, Germany) at 1 Hz.

3. Results and discussions

3.1. Microstructures, density and grain size of the samples

The microstructures of all samples of sintered BCZT-xCeO₂ ceramics were observed by SEM under sintering conditions of T₁-1400°C/30 min and T₂-1275°C/4 h as shown in Figure 1. All the CeO₂ concentrations were added in wt.% to the BCZT ceramics. It is evident that CeO₂ incorporation up to x = 0.07% causes high densification and uniform microstructures. As the sintering temperature increased further (T₁ = 1450°C/30 min), the samples with x = 0–0.04% became somewhat denser but sample x = 0.07% started to become porous, as seen in Figure 2. From that point on, we designated the *optimum sintering conditions*, i.e. T₁-1400°C/30 min and T₂-1275°C/4 h, as the temperatures at which the maximum relative density with a uniform microstructure were obtained.

The relative densities of BCZT-xCeO₂ ceramics treated under different sintering conditions are shown in Figure 3(a), which is in agreement with the microstructural analysis. As the Ce concentration increases, the relative density increases, and is achieved maximum (99%) of theoretical density (t.d. = 5.80 g/cm³ calculated from cell parameters), for sample x = 0.07 wt.%, under *optimum sintering conditions*, T₁-1400°C/30 min and T₂-1275°C/4 h. For pure BCZT (x = 0) however, a low relative density was observed (~94% of t.d.), even under higher sintering conditions. i.e. T₁-1450°C/30 min and T₂-1275°C/4 h. This clearly suggests that CeO₂ is an effective dopant for achieving high densification of BCZT ceramics at low temperature. The grain size calculations were conducted by the linear intercept method, as shown in Figure 3(b). The average grain size was observed to be ~8 µm for all the samples under different sintering conditions, indicating that the TSS technique could be useful in grain-size reduction

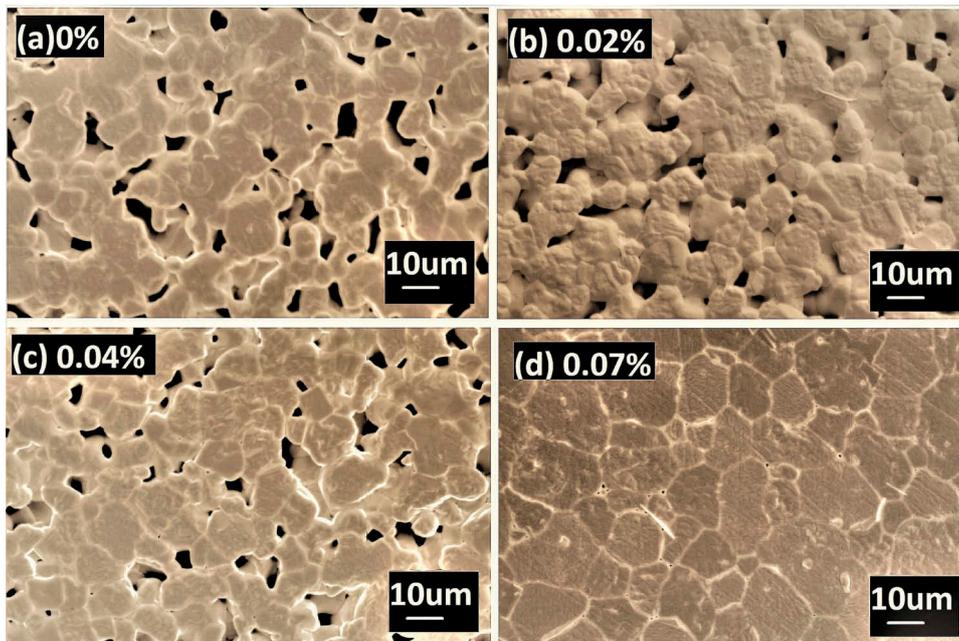


Figure 1. SEM microstructure of BCZT-xCeO₂ ceramics at sintering conditions of T₁-1400°C/30 min & T₂-1275°C/4 h.

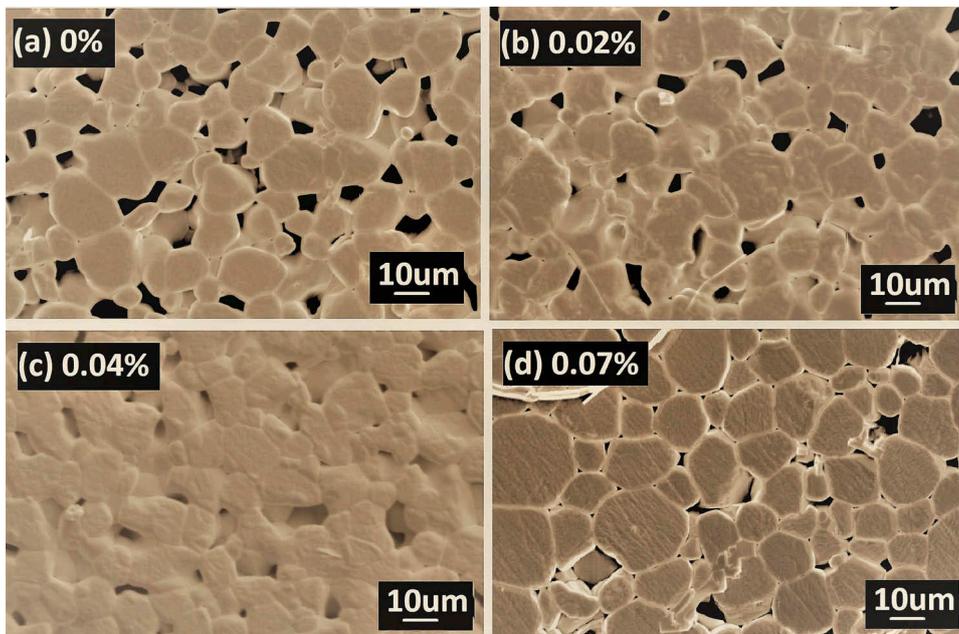


Figure 2. SEM microstructure of BCZT-xCeO₂ ceramics at sintering conditions of T₁-1450°C/30 min & T₂-1275°C/4 h.

and maintenance of a uniform microstructure. The average grain size for $x = 0.07\%$ under sintering conditions of T₁-1400°C & T₂-1275°C was 7.96 μm, which is slightly higher than that of such other lead-free piezoelectric materials as KNN and BNT (<3 μm) [4,31,32] but relatively lower than that of pure BCZT (grain size 8 μm) with almost 100% densification [33,34].

3.2. X-ray diffraction analysis and temperature-dependent relative permittivity

Figure 4(a) shows the X-ray diffraction patterns of BCZT-xCeO₂ ceramics produced under optimum sintering

conditions of T₁-1400°C & T₂-1275°C in the range of 20°-80° measured at room temperature (21°C). A pure perovskite crystal structure with no trace of a secondary phase was detected indicating that the CeO₂ ions had diffused into the BCZT lattice and formed a solid solution. The distinct sharp XRD peaks denote good homogeneity and crystallinity of the samples. For phase detection, further investigation of the XRD data was conducted by enlarging the 2θ angle between 44°-46° and 83°-85° as shown in Figure 4(b) & 4(c). The splitting of the (200) peak into (002)/(200) reflections at around 45° as well as a single peak (222) reflection at around 83.5° suggest single tetragonal phases (T) for all samples

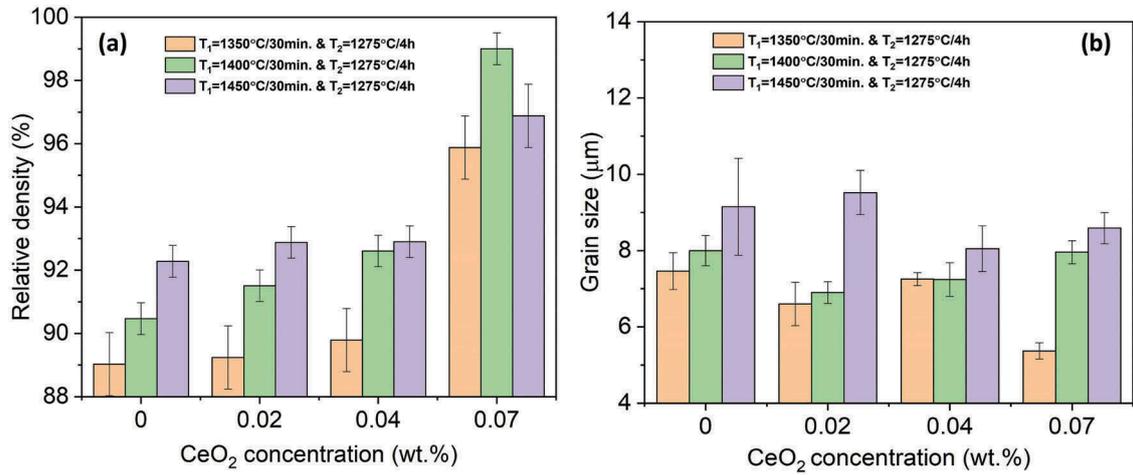


Figure 3. Relative densities and (b) grain sizes of BCZT-xCeO₂ ceramics at different sintering conditions.

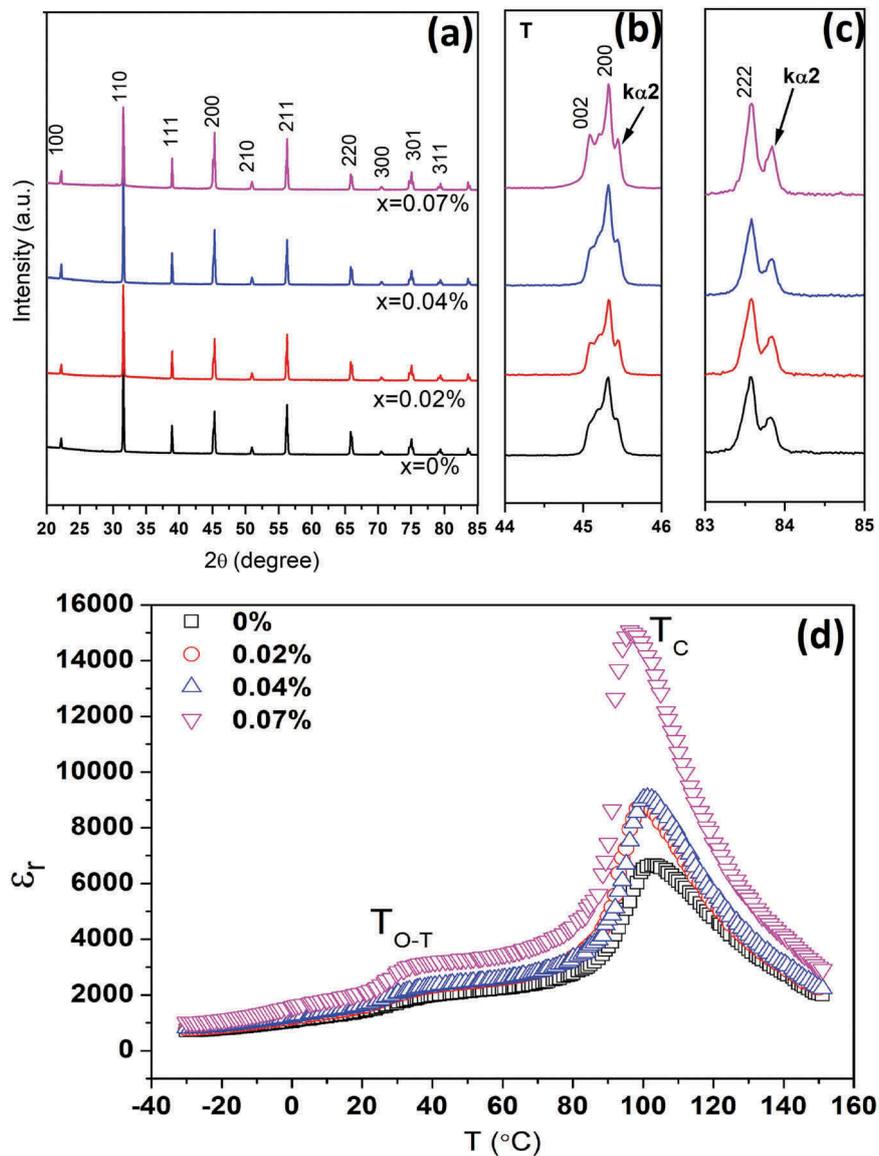


Figure 4. (a) XRD patterns between 20°-80°, (b) enlarged view of 2θ between 44°-46°, (c) enlarged view of 2θ between 83°-85° and (d) plot of dielectric permittivity with respect to temperatures of BCZT-xCeO₂ ceramics at sintering conditions of T₁-1400°C/30 min & T₂-1275°C/4 h min & T₂-1275°C/4 h.

Table 1. Cell parameters of BCZT-xCeO₂ ceramics at sintering conditions T₁-1400°C/30 min and T₂-1275°C/4 h.

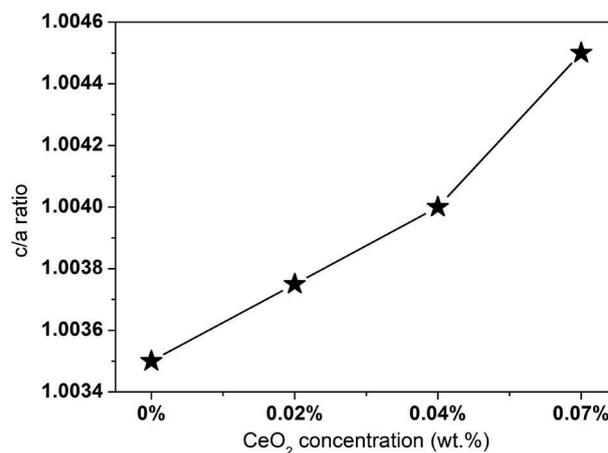
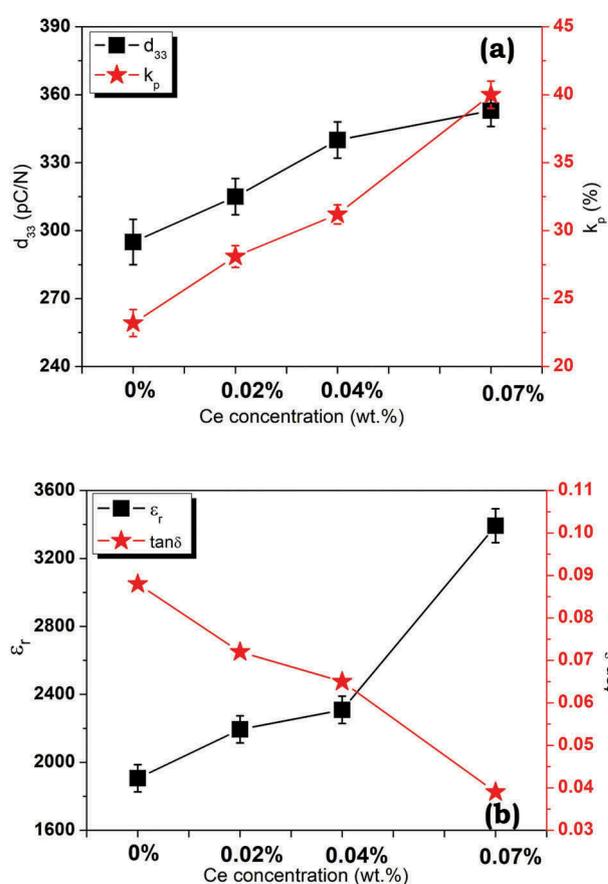
BCZT - xCeO ₂	a (Å)	c (Å)	Volume (cm ³)	c/a
0	3.998	4.012	64.138	1.0035
0.02	3.998	4.013	64.148	1.0037
0.04	3.998	4.014	64.168	1.0040
0.07	3.998	4.016	64.192	1.0045

provided by Rietveld analysis. All the reflections show an additional peak on the right side of the peaks corresponding to the Ka₂ reflection. It was therefore concluded that the low CeO₂ content (0–0.07%) did not affect the crystal structure of the BCZT ceramics. It is clear however that the tetragonality of the sintered samples increased with increase in the concentration of CeO₂. The cell parameters established by Rietveld refinement are listed in Table 1. We do not have the direct evidence of the orthorhombic phase in the XRD analysis as we obtained evidence from a temperature-dependent relative permittivity plot as discussed below. The reason is possibly the temperature at which the XRD measurement was conducted. We measured the XRD patterns at room temperature (21°C) while the orthorhombic-tetragonal (O-T) phase transition was found at around 32°C by the temperature dependent relative permittivity plot. Temperature dependent XRD measurement may therefore be conducted to analyze more precise phase identification which in future studies.

Figure 4(d) depicts the temperature dependent relative permittivity of BCZT-xCeO₂ ceramics measured at 1 kHz. All specimens undergo two-phase transitions, i.e. the orthorhombic-tetragonal phase transition (T_{O-T}) near 32°C and the tetragonal – cubic phase transition (T_C) at around 100°C. Similar results were obtained in our previous study [30]. A small amount of CeO₂ doping (x = 0.02–0.07%) did not change the crystal structure but significantly increased the relative permittivity (ε_r). The highest value for ε_r was observed as 15,067 for x = 0.07%, compared to 6659 found for x = 0%. The enhancement of relative permittivity may be attributed to the uniform grain sizes and highly dense microstructure caused by a small addition of CeO₂. T_C decreased slightly from ~103°C to nearly 96°C due to the compositional adjustment of Ce ions in the BCZT lattice. Moreover, the addition of CeO₂ led to a larger c/a ratio, as shown in Figure 5, which demonstrates that the tetragonality of these ceramics rises and phase boundary moves.

3.3. Piezoelectric and dielectric properties at room temperature

Figure 6(a,b) represents piezoelectric and dielectric properties of BCZT-xCeO₂ ceramics under sintering conditions of T₁-1400°C/30 min & T₂-1275°C/4 h. It can be clearly seen in Figure 6(a,b), that the planar coupling coefficient (k_p) and piezoelectric constant (d₃₃)

**Figure 5.** The c/a ratio as a function of the CeO₂ concentration at sintering conditions of T₁-1400°C/30 min & T₂-1275°C/4 h.**Figure 6.** (a) The piezoelectric coefficient and planer coupling coefficient and (b) the relative permittivity and dissipation factor as functions of the Ce concentration at sintering conditions of T₁-1400°C/30 min & T₂-1275°C/4 h.

increased with increase in the Ce concentration and achieved the maximum for the sample x = 0.07%, while the dissipation factor (tan δ) was reduced. The d₃₃ was altered from 295 ± 15 pC/N of x = 0% to 353 ± 7 pC/N of x = 0.07% and the dissipation factor was reduced from 0.088 to 0.039 units. In addition, k_p increased from 23.2 ± 2% to 40 ± 1%, while relative permittivity increased from 1906 ± 80 to 3393 ± 100 at room temperature. This improvement in d₃₃, k_p, and ε_r

Table 2. Physical, piezoelectric and dielectric properties of BCZT-xCeO₂ ceramics at sintering conditions T₁-1400°C/30 min and T₂-1275°C/4 h.

BCZT - xCeO ₂	Relative density (g/cm ³)	Grain Size (μm)	d ₃₃ (pC/N)	K _p (%)	ε _r	T _c (°C)
x = 0	90.47 ± 0.05	8.0 ± 0.75	295 ± 15	23.2 ± 2	1906 ± 80	103.4
x = 0.02	91.51 ± 0.05	6.9 ± 0.29	315 ± 10	28.1 ± 1	2193 ± 80	100.1
x = 0.04	92.61 ± 0.05	7.24 ± 0.44	340 ± 10	28.9 ± 2	2308 ± 80	101.2
x = 0.07	99.00 ± 0.05	7.96 ± 0.71	353 ± 7	40 ± 1	3393 ± 100	96.2

Table 3. Ferroelectric properties of BCZT-xCeO₂ ceramics at sintering conditions T₁-1400°C/30 min and T₂-1275°C/4 h.

BCZT- xCeO ₂ (in wt.%)	P _r (μC/cm ²)	P _{max} (μC/cm ²)	S _{max} (%)	E _c (kV/cm)
x = 0%	4.22	10.52	0.11	3.17
x = 0.02%	5.00	12.00	0.13	2.45
x = 0.04%	5.65	13.00	0.14	2.47
x = 0.07%	11.61	20.26	0.18	2.32

and the reduction in $\tan \delta$ were ascribed to the final ceramic density and uniform grain sizes. The piezoelectric and dielectric properties are summarized in Table 2. Previously, CeO₂ was used as an additive to PZT and BNBT materials [35,36], and it generally showed some effects on enhancing d₃₃ and reducing $\tan \delta$ at the same time. CeO₂ showed the same double effect here. The mechanism of CeO₂ on BCZT ceramics is more complex and is described in our previous study in detail [30]. Moreover, Ce ions possibly exist in two valence states, i.e. Ce³⁺ of the ionic radius 0.13 nm and Ce⁴⁺ of the ionic radius 0.087 nm. In view of the ionic radius, Ce³⁺ obviously cannot enter the B site of the BCZT perovskite structure but can occupy the A site. Thus, there are two possible cases: Ce³⁺ can enter either the Ca²⁺ position (ionic radius = 0.134 nm) or the Ba²⁺ position (ionic radius = 0.161 nm). If it occupies the Ca²⁺ site, the replacement of Ca²⁺ by Ce³⁺ does not cause deformation (due to the fact that the ionic radius of both ions are nearly the same) in the BCZT lattice to make an evident contribution to increasing the domain movement. If Ce³⁺ occupies Ba²⁺ (ionic radius = 0.161 nm) on the other hand, then Ce³⁺ may act as a donor dopant leading to some cation vacancies at the A site, which may facilitate domain wall movement in order to enhance the piezoelectric properties of BCZT ceramics. By contrast, Ce⁴⁺ has a smaller ionic radius (0.087 nm) compared to Ce³⁺ and can possibly occupy the B-site of either Ti⁴⁺ (0.060 nm) or Zr⁴⁺ (0.072 nm). When the CeO₂ concentration is low as in our case, the occupation by Ce⁴⁺ of the Ti⁴⁺ site cannot lead to O-vacancies and therefore does not explain the dissipation factor decrease by O-vacancy mechanism. Kolar et al. previously explained the Ce³⁺ and Ce⁴⁺ effects on BaTiO₃ solid solutions in detail [37]. They presented the basis for showing the possibility that one of the few cases that the Ce³⁺ donor charge could be compensated by a reduction of Ti⁴⁺ to Ti³⁺ (electronic compensation) by creation of ionizing vacancies at the Ti sites or by a combination of both mechanisms [38,39]. This results

in suppressing the movement of domains that cause a reduction in the dissipation factor ($\tan \delta$) [40].

3.4. Ferroelectric properties at room temperature

All ceramics show a polarization-electric (P-E) field loop as well as a current-electric field loop at sintering conditions of T₁-1400°C & T₂-1275°C, as depicted in Figure 7(a-d). For pure BCZT (x = 0%) a small remnant polarization (P_r = 4.22 μC/cm²) is observed with a relatively large coercive field (E_c) of 3.17 kV/cm. As the Ce content increased up to x = 0.07%, a large remnant polarization (P_r = 11.61 μC/cm²) with a low E_c = 2.32 kV/cm was observed. A low E_c suggest a soft nature of these ceramics, which indicates that Ce³⁺ acts as a donor dopant. The high P_r, may be attributable to large internal polarizability and large electromechanical coupling [41]. In addition, a sharp loop squareness generally indicates better homogeneity of grain sizes [41] as can be seen in Figure 7(d). Furthermore, I-E plot depicted in Figure 7(a-d), shows the switching process of these ceramics. For pure BCZT (x = 0%), the current peak intensity is low and broad, which indicates that the domain switching was not easy. A further increase in the Ce concentration (x = 0.02, 0.04%) provides some improvement in the current peak behavior and a sharp current peak was observed for the sample x = 0.07%. The width of the current peak gives the value of E_c at which remnant polarization could be obtained for ceramics [42,43]. Figure 8 represents the electric field induced strain loops for these ceramics. For sample x = 0.07%, a large strain (~0.18%) was observed under a 4 kV/mm positive electric field as compared to that of pure BCZT (x = 0%) as 0.11%. Such high bipolar strain values in a soft piezoelectric material may be attributable to easy domain motion. The ferroelectric properties are summarized in Table 3.

4. Conclusions

In this study, A sub-10 μm grain size and high-density (99%) uniform microstructure were obtained while maintaining good ferroelectric, dielectric and piezoelectric properties for BCZTCe ceramics via a two-step sintering technique. It has been reported that with TSS, grain size can be controlled (~8 μm) with a uniform microstructure. Addition of a small amount of CeO₂

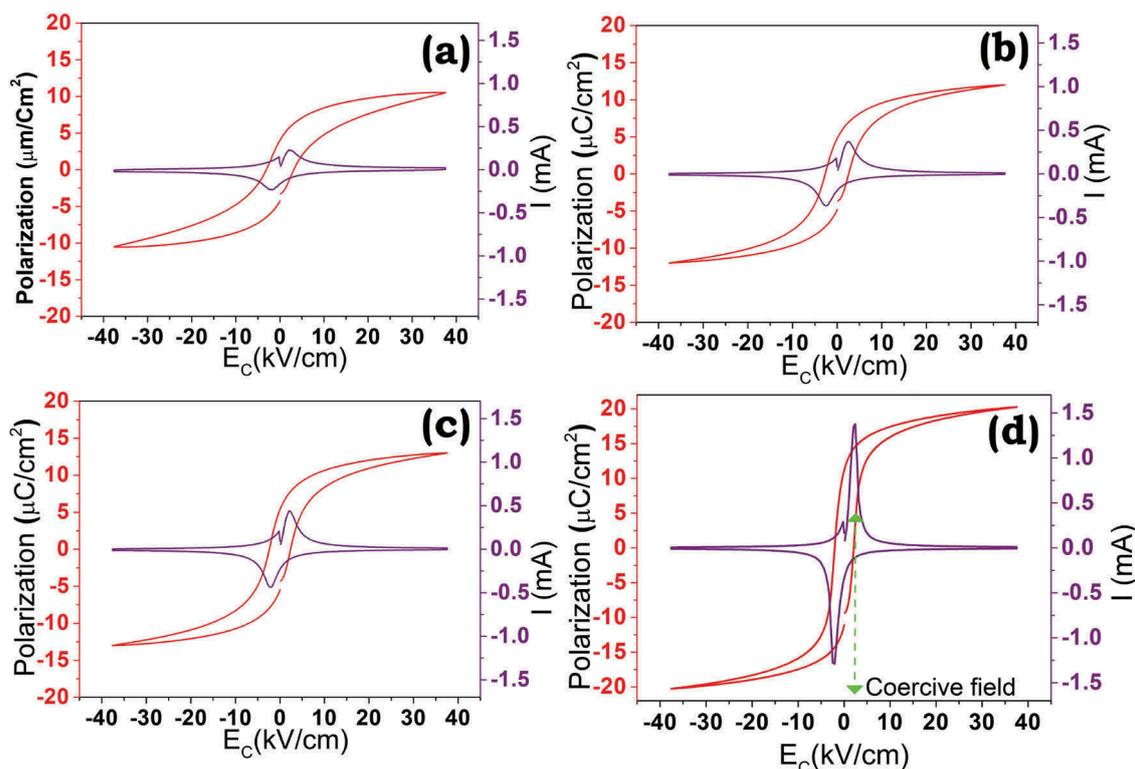


Figure 7. P-E hysteresis and I-E hysteresis responses for BCZT-xCeO₂ ceramics (a) $x = 0\%$ (b) $x = 0.02\%$ (c) $x = 0.04\%$ and, (d) $x = 0.07\%$ at sintering conditions of T_1 -1400°C/30 min & T_2 -1275°C/4 h.

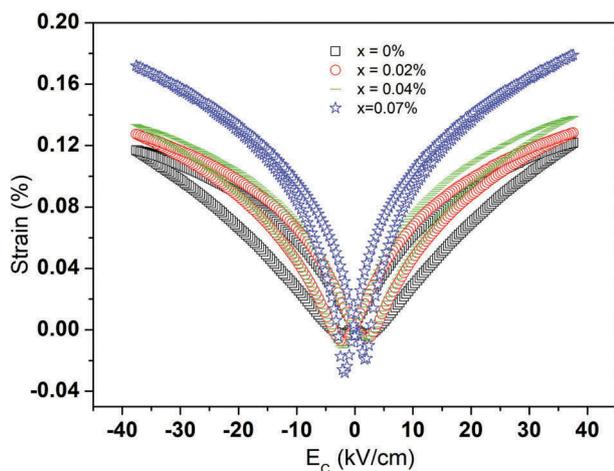


Figure 8. S-E curve for BCZT-xCeO₂ ($x = 0$ –0.07 wt.%) ceramics at sintering conditions of T_1 -1400°C/30 min & T_2 -1275°C/4 h.

significantly reduced the sintering temperature as well as helping densification (relative density $\sim 99\%$) which led to maintenance of good properties potentially suited to the fabrication of technological devices. The optimal properties were obtained for $x = 0.07$ wt.% at sintering conditions of $T_1 = 1400^\circ\text{C}$ & $T_2 = 1275^\circ\text{C}/4$ h, in which $d_{33} = 353 \pm 7$ pC/N, $k_p = 40\%$, $\epsilon_r = 3393 \pm 100$, $\tan \delta = 0.039$, $T_C = 96.5^\circ\text{C}$, $P_r = 11.45 \mu\text{C}/\text{cm}^2$ and $E_C = 2.32$ kV/cm with an average grain size ~ 7 – $8 \mu\text{m}$. These results strongly suggest that TSS is an effective sintering method for grain-size reduction with a uniform microstructure and that CeO₂ is a suitable dopant for reducing the sintering temperature as well as achieving enhanced density of BCZT ceramics.

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Disclosure statement

No potential conflict of interest was reported by the authors.

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